

ESD Protection Diodes Silicon Epitaxial Planar

DF2B5M4SL

1. General

The DF2B5M4SL is a TVS diode (ESD protection diode) protects semiconductor devices used in mobile device interfaces and other applications to protect against static electricity and noise.

Utilizing snapback characteristics, the DF2B5M4SL provides low dynamic resistance and superior protective performance.

Furthermore, it is optimum the high speed signal application for the low capacitance performance. The DF2B5M4SL is housed in an ultra-compact package (0.32 mm × 0.62 mm) to meet applications that require a small footprint.

2. Applications

Mobile Equipment

- Smartphones
- Tablets
- Notebook PCs

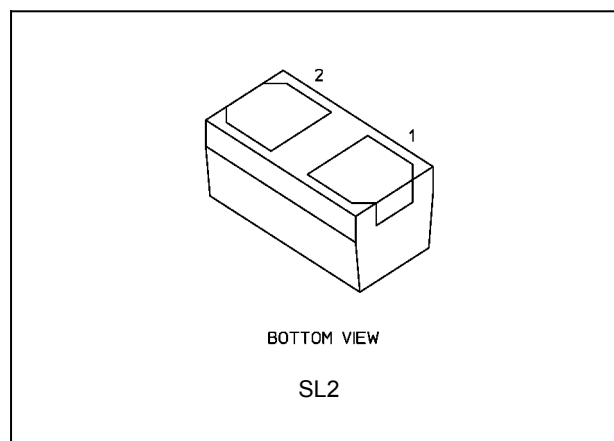
Desktop PCs

Note: This product is designed for protection against electrostatic discharge (ESD) and is not intended for any other purpose, including, but not limited to, voltage regulation.

3. Features

- (1) Suitable for use with a 3.3 V signal line. ($V_{RWM} \leq 3.6$ V)
- (2) Protects devices with its high ESD performance.
($V_{ESD} = \pm 20$ kV (Contact / Air) @IEC61000-4-2)
- (3) Low dynamic resistance protects semiconductor devices from static electricity and noise.
($R_{DYN} = 0.5 \Omega$ (typ.))
- (4) Snapback characteristics realizing low clamping voltage protects semiconductor devices.
($V_C = 10$ V@ $I_{PP} = 2$ A (typ.))
- (5) Compact package is suitable for use in high density board layouts such as in mobile devices.
(0.32 mm × 0.62 mm size (Toshiba package name: SL2))

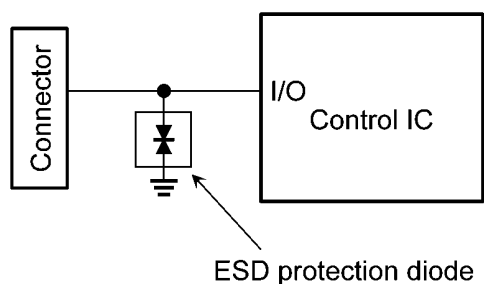
4. Packaging



Start of commercial production

2015-09

5. Example of Circuit Diagram



6. Quick Reference Data

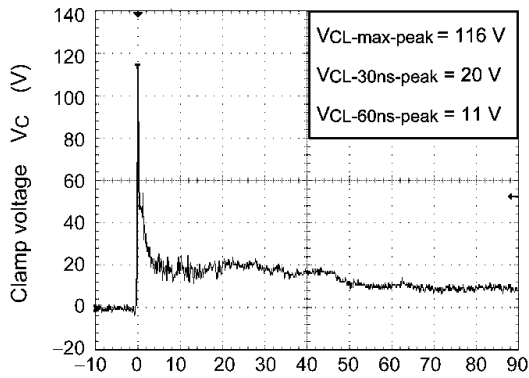
Characteristics	Symbol	Note	Test Condition	Min	Typ.	Max	Unit
Working peak reverse voltage	V_{RWM}	(Note 1)	—	—	—	3.6	V
Total capacitance	C_t		$V_R = 0\text{ V}$, $f = 1\text{ MHz}$	—	0.2	0.3	pF
Dynamic resistance	R_{DYN}	(Note 2)	—	—	0.5	—	Ω
Electrostatic discharge voltage (IEC61000-4-2) (Contact)	V_{ESD}	(Note 3)	—	—	—	20	kV

Note 1: Recommended operating condition.

Note 2: TLP parameters: $Z_0 = 50\ \Omega$, $t_p = 100\text{ ns}$, $t_r = 300\text{ ps}$, averaging window: $t_1 = 30\text{ ns}$ to $t_2 = 60\text{ ns}$, extraction of dynamic resistance using least squares fit of TLP characteristics between $I_{PP1} = 8\text{ A}$ and $I_{PP2} = 16\text{ A}$.

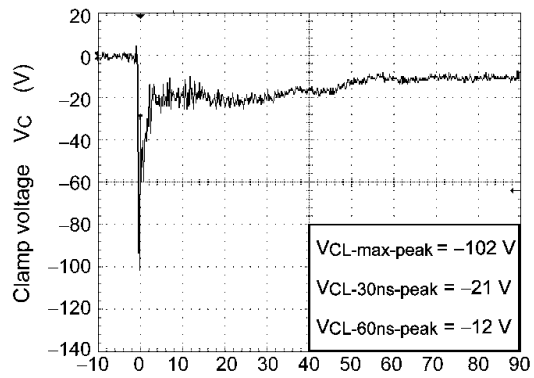
Note 3: Criterion: No damage to devices.

6.1. ESD Clamp Waveform (Note)



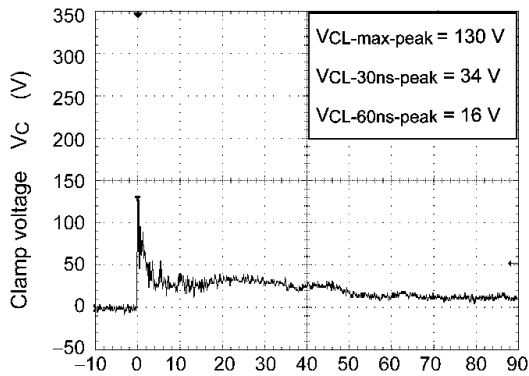
Pulse time t_p (ns)

Fig. 6.1.1 +8 kV



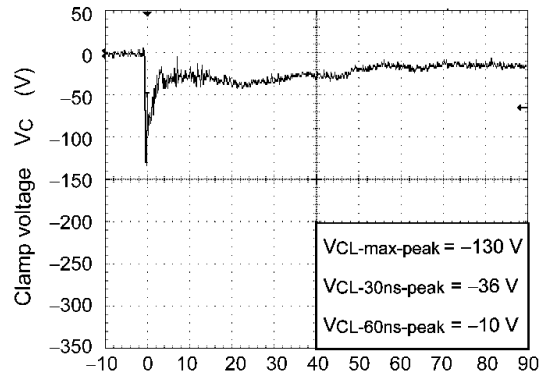
Pulse time t_p (ns)

Fig. 6.1.2 -8 kV



Pulse time t_p (ns)

Fig. 6.1.3 +15 kV



Pulse time t_p (ns)

Fig. 6.1.4 -15 kV

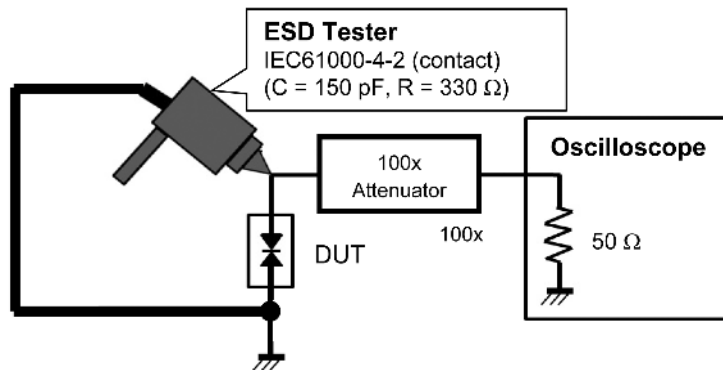
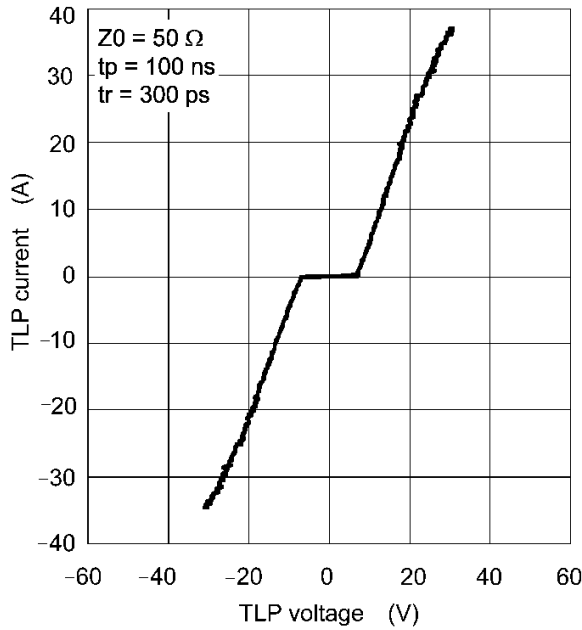


Fig. 6.1.5 IEC61000-4-2 (Contact)

Note: The above characteristics curves are presented for reference only and not guaranteed by production test, unless otherwise noted.

6.2. TLP Characteristics (Note)



Note: The above characteristics curves are presented for reference only and not guaranteed by production test, unless otherwise noted.

6.3. Clamp Voltage - Peak Pulse Current ($V_C - I_{PP}$) (Note)

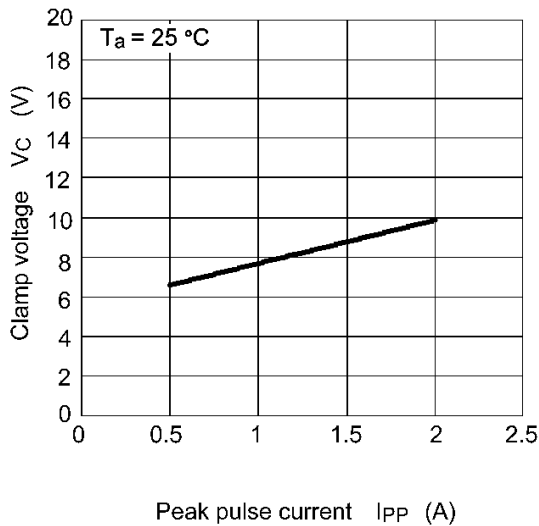


Fig. 6.3.1 $V_C - I_{PP}$

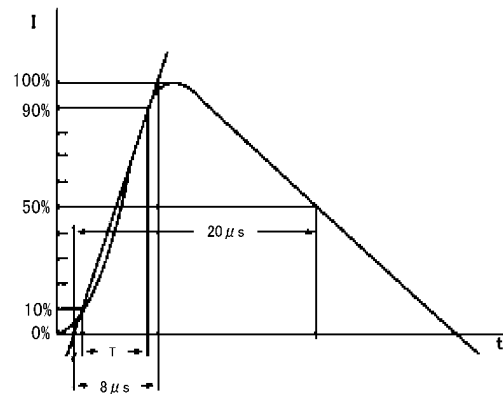


Fig. 6.3.2 Based on IEC61000-4-5 8/20 μs pulse.

Note: The above characteristics curves are presented for reference only and not guaranteed by production test, unless otherwise noted.

7. Absolute Maximum Ratings (Note) (Unless otherwise specified, $T_a = 25\text{ }^\circ\text{C}$)

Characteristics	Symbol	Note	Rating	Unit
Electrostatic discharge voltage (IEC61000-4-2) (Contact)	V_{ESD}	(Note 1)	± 20	kV
Electrostatic discharge voltage (IEC61000-4-2) (Air)			± 20	
Peak pulse power ($t_p = 8/20\ \mu\text{s}$)	P_{PK}		30	W
Peak pulse current ($t_p = 8/20\ \mu\text{s}$)	I_{PP}	(Note 2)	2.0	A
Junction temperature	T_j		150	$^\circ\text{C}$
Storage temperature	T_{stg}		-55 to 150	$^\circ\text{C}$

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc.).

Note 1: According to IEC61000-4-2.

Note 2: According to IEC61000-4-5.

8. Electrical Characteristics (Unless otherwise specified, $T_a = 25\text{ }^\circ\text{C}$)

V_{RWM} : Working peak reverse voltage
 V_{BR} : Reverse breakdown voltage
 I_{BR} : Reverse breakdown current
 I_R : Reverse current
 V_C : Clamp voltage
 I_{PP} : Peak pulse current
 R_{DYN} : Dynamic resistance

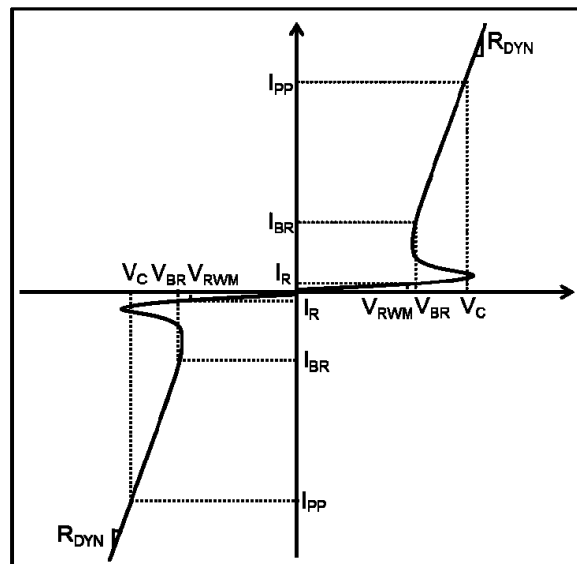


Fig. 8.1 Definitions of Electrical Characteristics

Characteristics	Symbol	Note	Test Condition	Min	Typ.	Max	Unit
Working peak reverse voltage	V_{RWM}	(Note 1)	—	—	—	3.6	V
Total capacitance	C_t		$V_R = 0\text{ V}$, $f = 1\text{ MHz}$	—	0.2	0.3	pF
Dynamic resistance	R_{DYN}	(Note 2)	—	—	0.5	—	Ω
Reverse breakdown voltage	V_{BR}		$I_{BR} = 1\text{ mA}$	4.0	5.0	6.0	V
Reverse current	I_R		$V_{RWM} = 3.6\text{ V}$	—	—	0.1	μA
Clamp voltage	V_C	(Note 3)	$I_{PP} = 1\text{ A}$	—	7.5	—	V
			$I_{PP} = 2\text{ A}$	—	10	15	V
		(Note 2)	$I_{TLP} = 16\text{ A}$	—	17	—	V
			$I_{TLP} = 30\text{ A}$	—	24	—	V

Note 1: Recommended operating condition.

Note 2: TLP parameters: $Z_0 = 50\ \Omega$, $t_p = 100\text{ ns}$, $t_r = 300\text{ ps}$, averaging window: $t_1 = 30\text{ ns}$ to $t_2 = 60\text{ ns}$, extraction of dynamic resistance using least squares fit of TLP characteristics between $I_{PP1} = 8\text{ A}$ and $I_{PP2} = 16\text{ A}$.

Note 3: Based on IEC61000-4-5 8/20 μs pulse.

9. Characteristics Curves (Note)

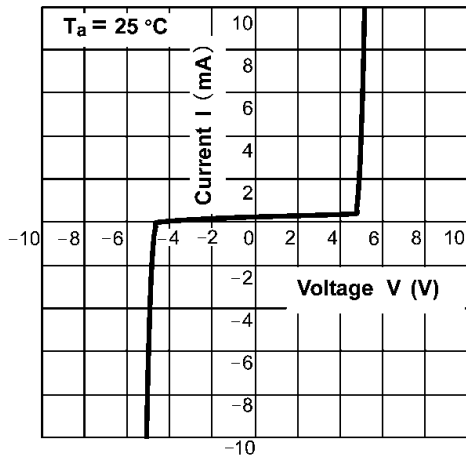


Fig. 9.1 I - V

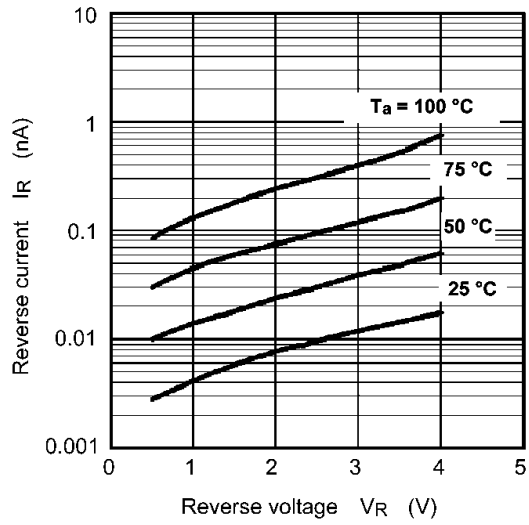


Fig. 9.2 $I_R - V_R$

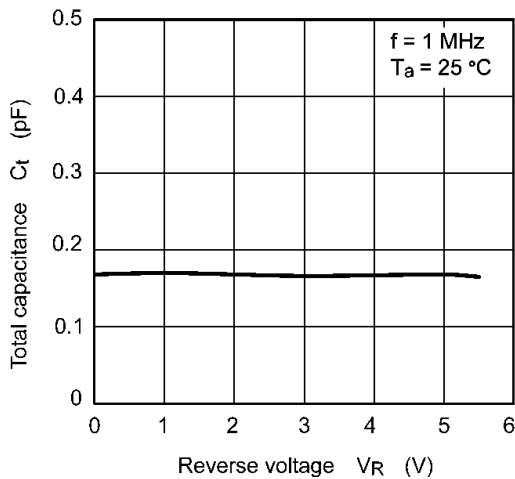


Fig. 9.3 $C_t - V_R$

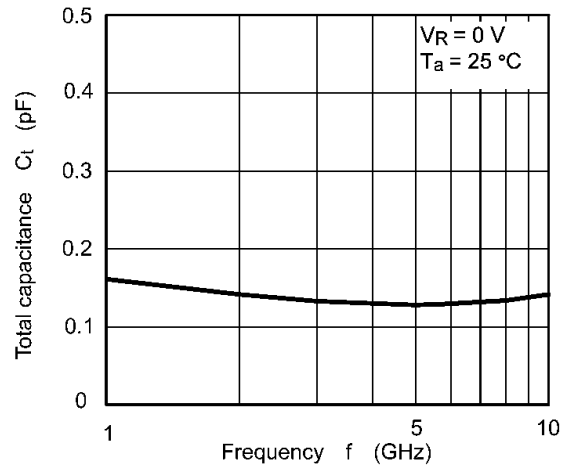


Fig. 9.4 $C_t - f$

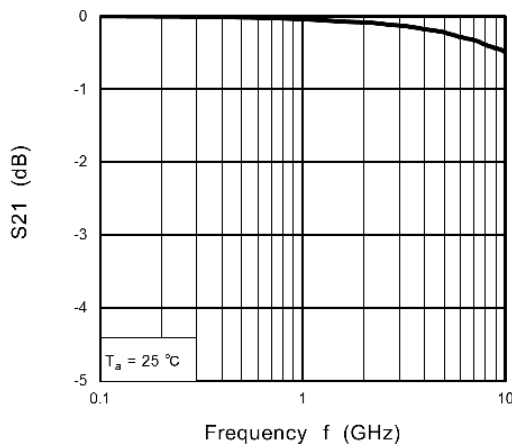
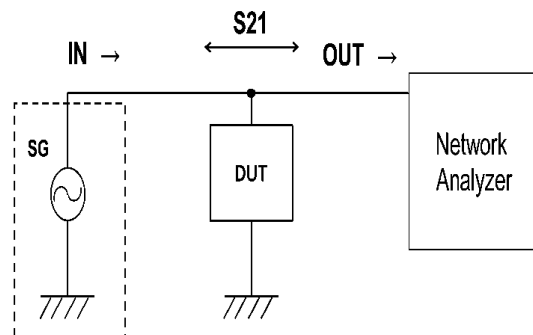
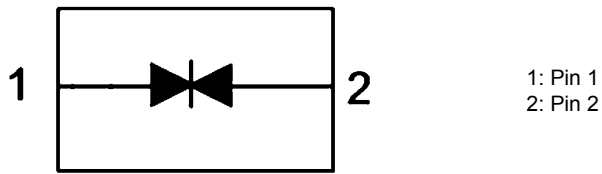


Fig. 9.5 $S_{21} - f$



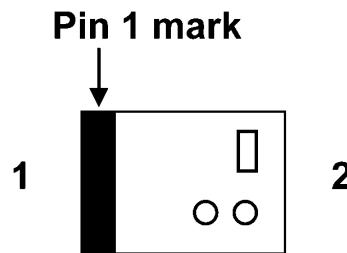
Note: The above characteristics curves are presented for reference only and not guaranteed by production test, unless otherwise noted.

10. Internal Circuit (Note)

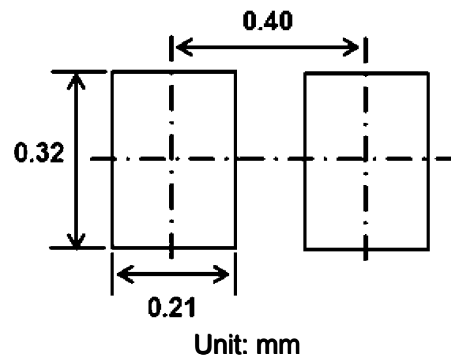


Note: Connect Pin 2 to GND when using Pin 1 for I/O.
Connect Pin 1 to GND when using Pin 2 for I/O.

11. Marking (Top view)

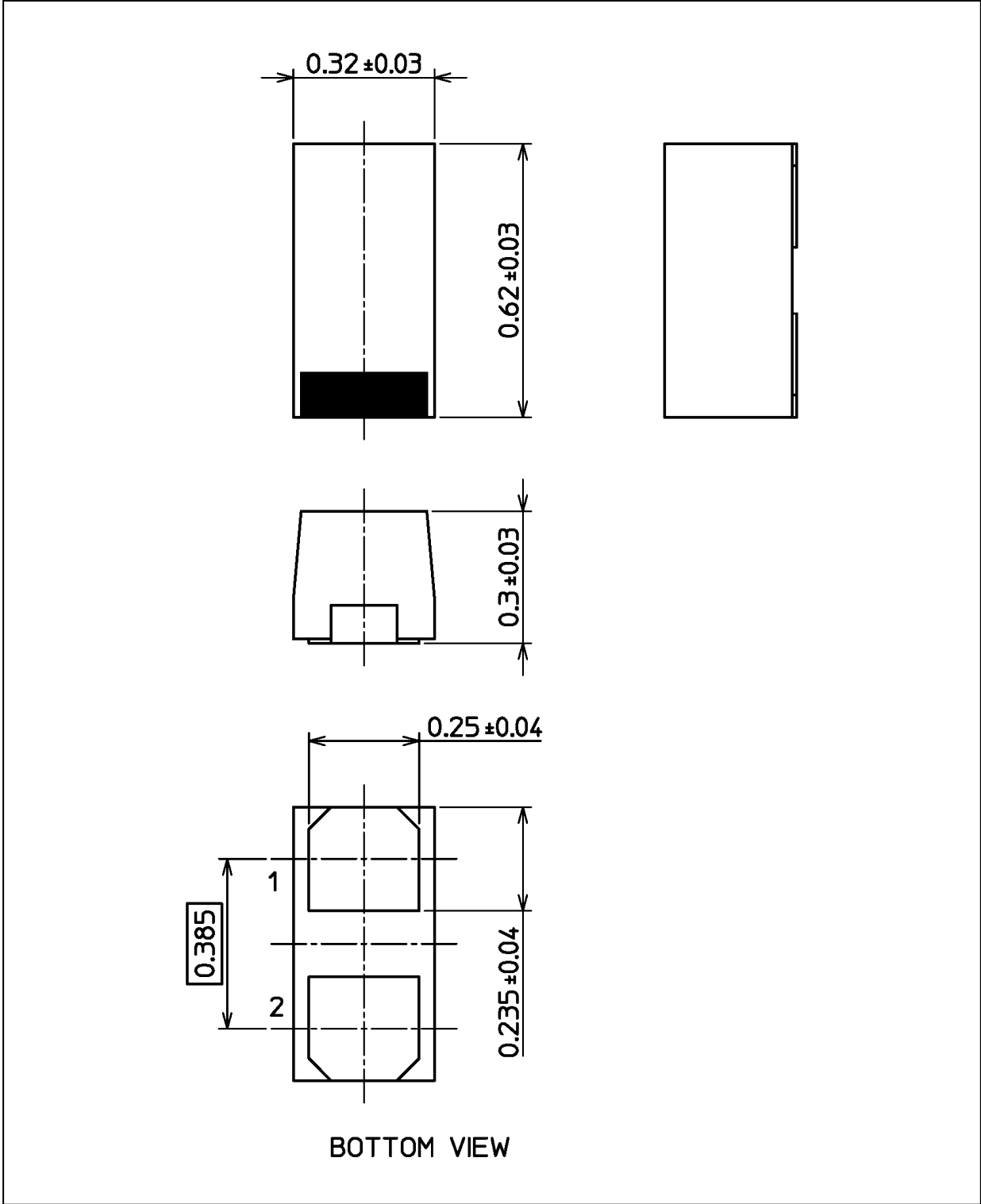


12. Land Pattern Dimensions (for reference only)



Package Dimensions

Unit: mm



Weight: 0.2 mg (typ.)

Package Name(s)
Nickname: SL2

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